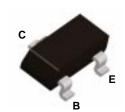


Discrete POWER & Signal **Technologies**

FSBCW30



SuperSOT™-3

PNP General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See BC857A for characteristics.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	32	V
V _{CBO}	Collector-Base Voltage	32	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		FSBCW30	
P _D	Total Device Dissipation	500	mW
	Derate above 25°C	4	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

^{*}Device mounted on FR-4 PCB 4.5" x 5"; mounting pad 0.02 in² of 2oz copper.

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

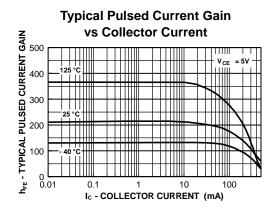
PNP General Purpose Amplifier (continued)

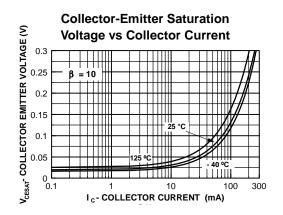
Symbol	Parameter	Test Conditions	Min	Max	Units
			ı	<u>I</u>	I.
OFF CHA	RACTERISTICS				
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 2.0 \text{ mA}, I_B = 0$	32		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 10 μA, I _E = 0	32		V
BV _{CES}	Collector-Emitter Breakdown Voltage	$I_C = 10 \ \mu A, I_E = 0$	32		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 10 μA, I _C = 0	5.0		V
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 32 \text{ V}, I_{E} = 0$ $V_{CB} = 32 \text{ V}, I_{E} = 0, T_{A} = +100$ °C		100 10	nA μA
ON CHAR	ACTERISTICS				
h _{FE}	DC Current Gain	$V_{CE} = 5.0 \text{ V}, I_{C} = 2.0 \text{ mA}$	215	500	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$		0.30	V
V _{BE(on)}	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 2.0 \text{ mA}$	0.60	0.75	V
SMALL S	IGNAL CHARACTERISTICS				
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_C = 200 \mu\text{A}, \\ R_S = 2.0 \text{ k}\Omega, \ f = 1.0 \text{ kHz}, \\ B_W = 200 \text{ Hz}$		10	dB

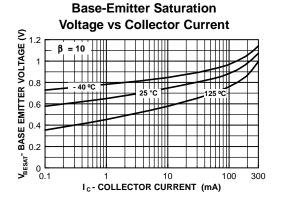
PNP General Purpose Amplifier

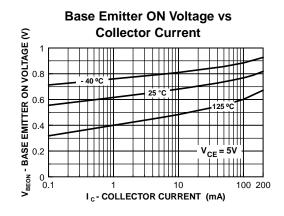
(continued)

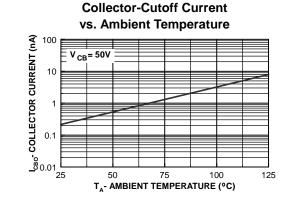
Typical Characteristics

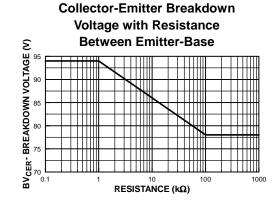








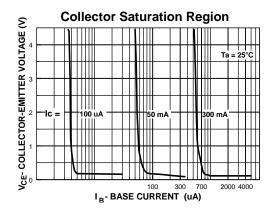




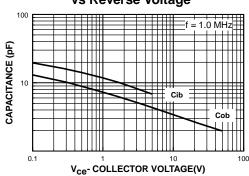
PNP General Purpose Amplifier

(continued)

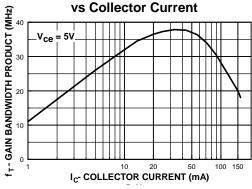
Typical Characteristics (continued)



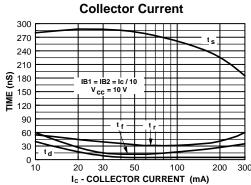
Input and Output Capacitance vs Reverse Voltage



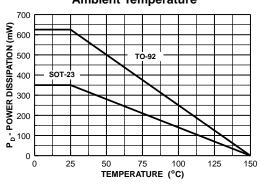
Gain Bandwidth Product



Switching Times vs



Power Dissipation vs Ambient Temperature



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 $\begin{array}{lll} \mathsf{FACT} \ \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} & \mathsf{Quiet} \ \mathsf{Series^{\mathsf{TM}}} \\ \mathsf{FAST}^{\tiny{\textcircled{\tiny{\$}}}} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-3} \\ \mathsf{FASTr^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-6} \\ \mathsf{GTO^{\mathsf{TM}}} & \mathsf{SuperSOT^{\mathsf{TM}}}\text{-8} \\ \mathsf{HiSeC^{\mathsf{TM}}} & \mathsf{TinyLogic^{\mathsf{TM}}} \end{array}$

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PRODUCT STATUS DEFINITIONS

Definition of Terms

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.